

Dr. Laurent Grenouillet received the Engineer degree in physics in 1998 from the National Institute of Applied Sciences (INSA) in Lyon, France, and the PhD degree in electronic devices in 2001 for his work on the optical spectroscopy of diluted nitrides grown on GaAs substrates.

After a post-doctoral position in the field of Molecular Beam Epitaxy, he joined CEA-Leti in 2002 and worked on GaAs-based VCSELs emitting in the 1.1-1.3 μ m range and single photon sources with quantum dots. In 2006, he joined the Silicon Photonics group where he developed CMOS compatible hybrid III-V on silicon lasers. In 2009, he joined IBM Alliance in Albany as a Leti assignee to contribute to the development of FDSOI technology. Within Albany state-of-the-art facilities, he extensively worked on device integration to improve performance of FDSOI devices (28nm and 14nm node).

Back in France at CEA-LETI in 2013, he focused on the performance boosters for the 10nm node FDSOI technology, and took part to the FDSOI technology transfer to Global Foundries (22FDX) in 2015. During that period he joined the Memory Laboratory to explore OxRAM memories and how those non-volatile memories can be integrated with FDSOI transistors.

Laurent Grenouillet authored or co-authored over 80 papers (conferences and journals) and has filed over 35 patents. He serves as committee member of Solid-State Devices and Materials (SSDM) conference and SOI-3D-Subthreshold Microelectronics Technology Unified (S3S) conference.